

PHOTOLUMINESCENCE STUDIES OF II-VI SEMICONDUCTORS, P.A. Egeler¹, M. Dobrowolska*², M. Kutrowski², L. Titova², and R. Chakarvorty², Northern Michigan University¹, Physics Department, Marquette, MI 49855, University of Notre Dame², Department of Physics, Notre Dame, IN 46556, pegeler@nmu.edu

Photoluminescence (PL) is a fast and non-destructive method of characterizing the quality of semiconductor samples. PL was used to determine the quality of II-VI semiconductors grown by Molecular Beam Epitaxy (MBE). Samples of ZnBeSe/ZnCdSe and ZnSe:Cl were grown and tested with these techniques. Of particular interest in the case of ZnBeSe/ZnCdSe is the formation of quantum wells to be used in other experiments. Results of these studies will be presented and future plans to improve the quality of the quantum wells will be discussed.

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